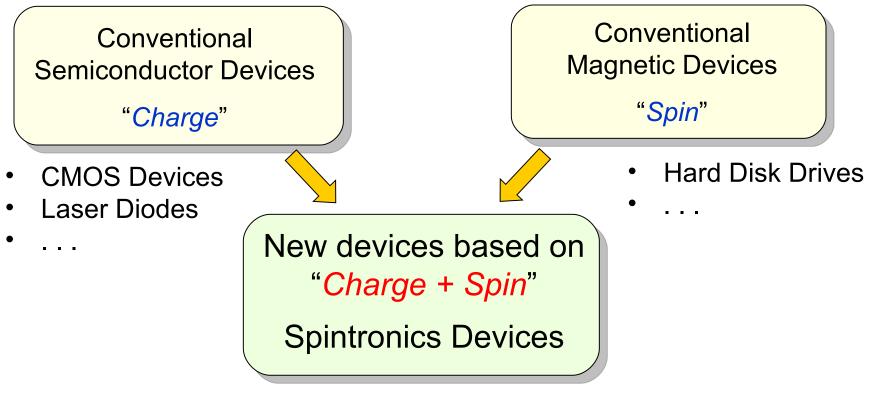
Effects of Electron-Electron Interaction on the Transport in Spintronic Devices

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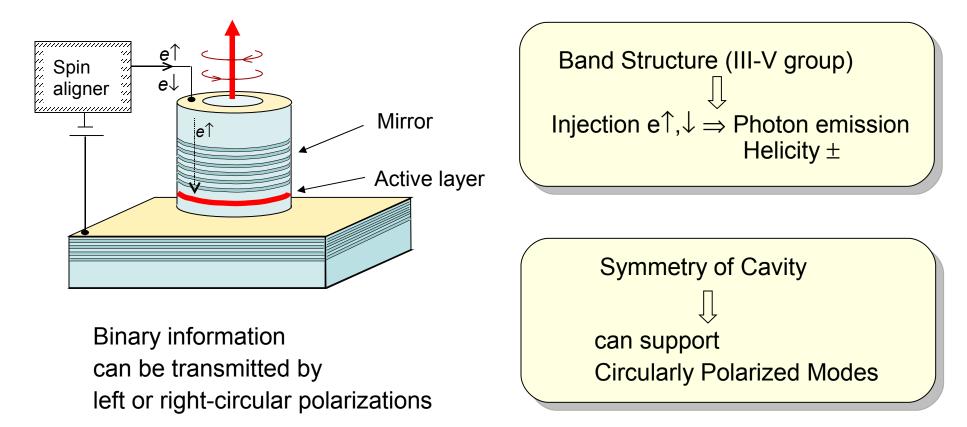
Electronics Devices Work on Electrons



- Spin FET
- Spin Laser Diode
- •

- GMR Devices
- TMR Devices
- Magnetoresistive RAM
- . . .

Spin LD : Vertical-Cavity Surface-Emitting Laser



Transport Mechanism of Spin-Polarized Electrons in Devices

Does the Carrier Transport Depend on Electron-Electron Scattering?

Transport in Unpolarized System

Mobility is determined by

- *e*-impurity (low temp.)
- *e*-phonon (higher temp.) but

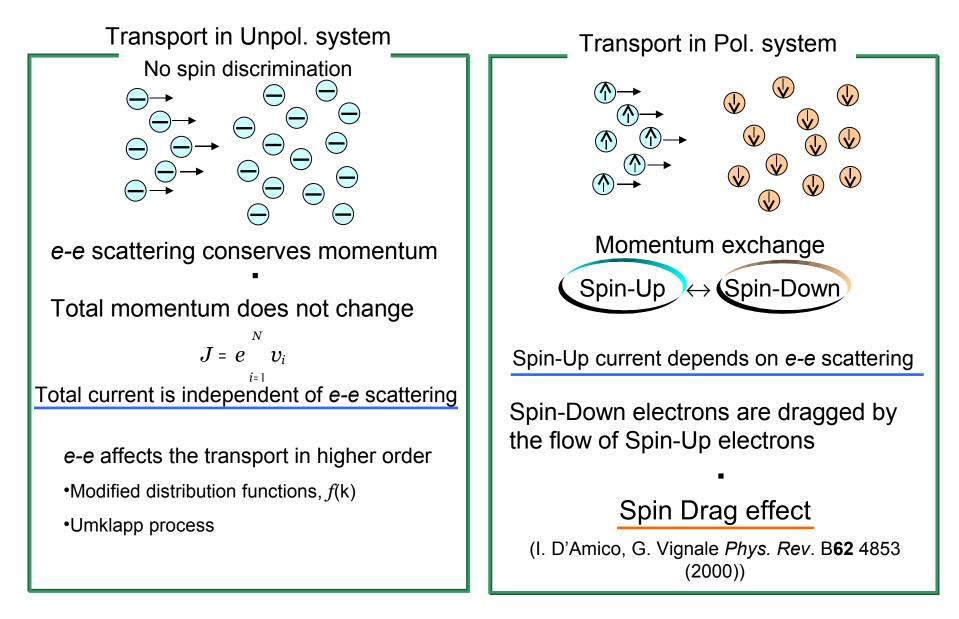
DUT

* e-e interaction does not affect, [to the lowest order] Transport in Spin-Polarized System

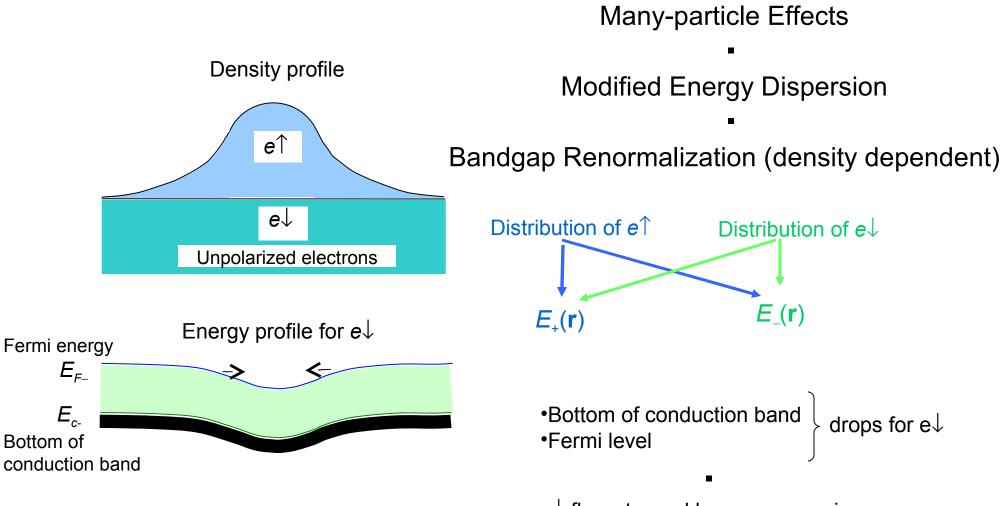
Spin transport is determined by

- *e*-impurity (low temp.)
- *e*-phonon (higher temp.) *also by*
- * e-e interaction

Effect 1: Spin Drag by Electron-Electron Collisions

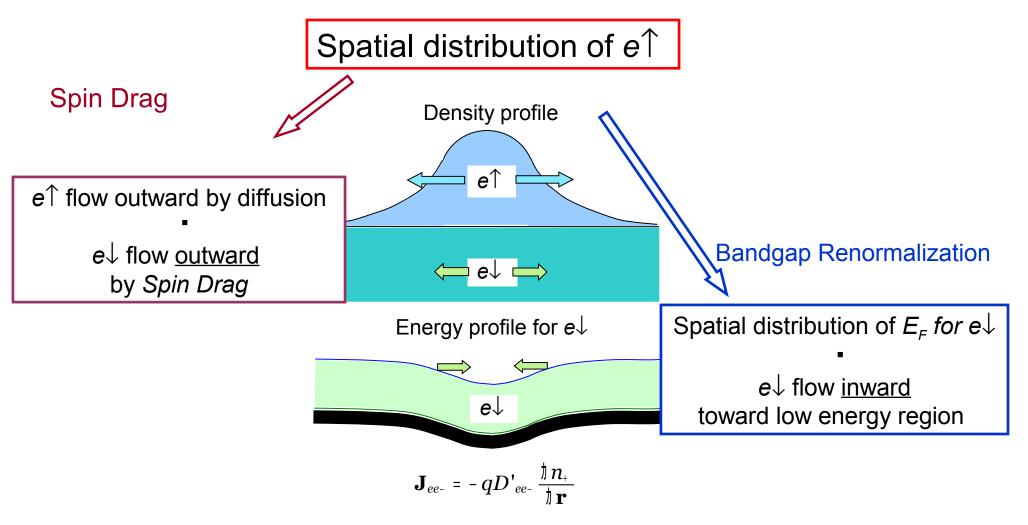


Effect2: caused by Bandgap Renormalization



 $e\downarrow$ flows toward low energy region

Competition of Spin Drag and Bandgap Renormalization



Positive contribution from \Rightarrow D'_{ee-} \leftarrow Negative contribution fromSpin DragBandgap Renormalization

Theory

Full quantum mechanical transport equation

Quantum transport eq. from nonequilibrium Green's functions

- Distribution functions 2 x 2 in spinor space
 - Electron spin is treated exactly in quantum mechanics
- Many-particle effects included in the RPA order
 - Band dispersions are modified differently for e^{\uparrow} and e^{\downarrow} when $n_{+} \neq n_{-}$
 - G.D. Mahan *Many-Particle Physics* (3rd ed.) (§8-5)
 - H. Haug, A. Jauho Quantum Kinetics in Transport and Optics of Semicondnuctors
 - Y. Takahashi *et al.*, Phys. Rev. B **60** (7) 4856 (1999)

Transport equation

$$\frac{\hbar \overline{\mu}_{+}}{\hbar \mathbf{r}} = -\mathbf{j}_{+} \frac{m}{n_{+}} \frac{\mathbf{m}}{\mathbf{n}_{+}} \frac{\mathbf{m}}{\mathbf{\tau}_{+}} + \frac{1}{\tau_{ex+}} + \mathbf{j}_{-} \frac{m}{n_{+} \tau_{-}}$$
$$\frac{\hbar \overline{\mu}_{-}}{\hbar \mathbf{r}} = -\mathbf{j}_{-} \frac{m}{n_{-}} \frac{\mathbf{m}}{\mathbf{n}_{+}} \frac{1}{\tau_{ex-}} + \frac{1}{\tau_{ex-}} + \mathbf{j}_{+} \frac{m}{n_{-} \tau_{+}}$$

$$\begin{split} \bar{\mu}_{1}(\mathbf{r}) &= \mu_{1}(\mathbf{r}) + q\phi(\mathbf{r}) &: \text{ electrochemical potential } (\mu_{\pm}(\mathbf{r}): \text{ chemical potential}) \\ q: & \text{charge} \\ m: & \text{band effective mass} \\ \phi(\mathbf{r}): & \text{electrical potential} \\ \mathbf{j}_{\pm} &= \mathbf{J}_{\pm}/q: & \text{current of spin-up/down electrons} \quad (\mathbf{J}_{+} + \mathbf{J}_{-}: \text{ total charge current}) \\ n_{\pm}(\mathbf{r}): & \text{distribution function for spin-up/down electrons} \\ \boldsymbol{\xi}_{x\pm} &= (1/\tau_{ion\pm} + 1/\tau_{ph\pm})^{-1} \end{split}$$

- $\underline{\tau}$: relaxation time for *e-e* scattering
- $T_{mp_{\pm}}$: relaxation time for *electron-impurity* scattering

 $T_{bh\pm}$: relaxation time for *electron-phonon* scattering

Drift transport driven by electric field (Mobilities)

- Electrons are driven by external field
- Homogeneous electron distributions

No effect from Bandgap Renormalization

 $\mathbf{J}_{7} = n_{7} q \underline{\mu_{nee7}} \mathbf{E}$ $\mu_{nee\pm} = \mu_{n\pm} \mathbf{x} \text{ (Correction Factor for e-e scattering)}$ $\min \left\{ \mathbf{M}_{n7} = \frac{q \tau_{ex7}}{m} \right\}$ $\mathbf{Spin Drag modifies mobilities:}$ $\mu_{n\pm} \Rightarrow \mu_{nee\pm}$

Diffusion transport driven by density gradient

- Electron density depends on position
- Currents are driven by density gradient

affected by both Spin Drag and Band Renormalization

2. Driving term :
$$\frac{\hbar \mu_{1}}{\hbar \mathbf{r}} = \frac{\hbar \mu_{1}}{\hbar n_{7}} \frac{\hbar n_{7}}{\hbar \mathbf{r}} + \frac{\hbar \mu_{1}}{\hbar n_{\mp}} \frac{\hbar n_{\mp}}{\hbar \mathbf{r}}$$
3. Current :
> without e-e $\mathbf{J}_{1} = -qD_{7} \frac{\hbar n_{7}}{\hbar \mathbf{r}}$ (Fick's law) $(D_{\pm}$: Diffusion coefficient)
> e-e included $\mathbf{J}_{ee^{7}} = -qD_{ee^{7}} \frac{\hbar n_{7}}{\hbar \mathbf{r}} - qD'_{ee^{7}} \frac{\hbar n_{\mp}}{\hbar \mathbf{r}}$ ($D_{ee\pm}$: modified Dif. coefficient)

Spin-Down current is modified by the distribution of Spin-Up electrons.

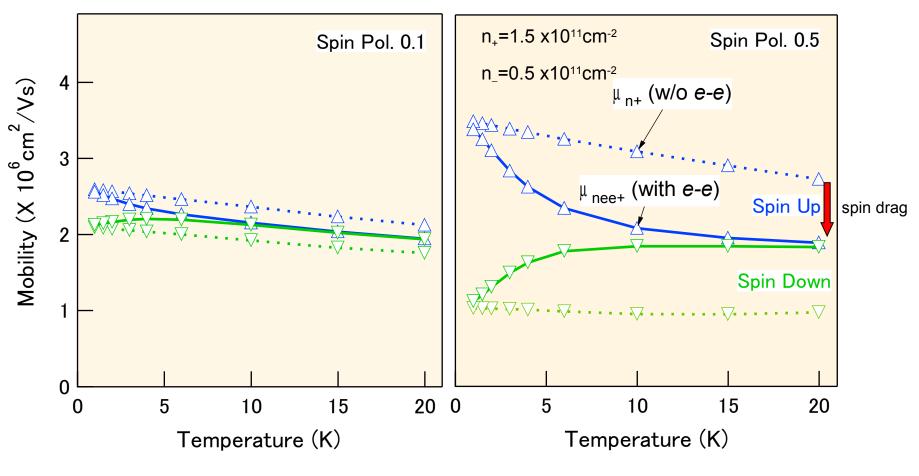
Modulation-doped 2D Electron Gas in GaAs/AlGaAs heterostructures

- Carrier density $(n_+ + n_-)$: 2 x 10¹¹ cm⁻²
- Spin polarization $(P = \frac{n_+ n_-}{n_+ + n_-})$: 0.0 ~ 0.5
- Temperature : $1 \text{ K} \sim 20 \text{ K} (<< T_F)$ Electrons are degenerate

Scattering processes

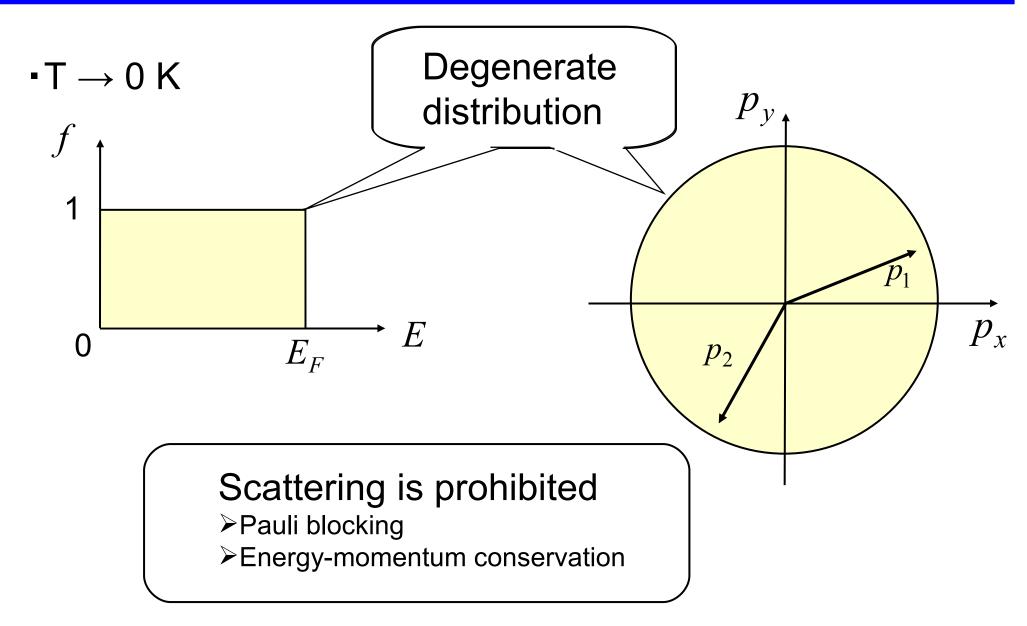
- 6. electron-impurity scattering
 - i. Scattering by remote impurities (modulation-dopants, 50 nm from the 2DEG)
 - Scattering by inplane impurities (residual impurities: 1 x 10⁸ cm⁻²)
- 7. electron-phonon scattering
 - acoustic phonon scattering by deformation potential
- 8. electron-electron scattering by RPA-screened Coulomb interaction

Electron mobilities $\mu_{nee\pm}$ vs. $\mu_{n\pm}$ at electron density $n_{\pm} + n_{\pm} = 2 \times 10^{11} \text{ cm}^{-2}$

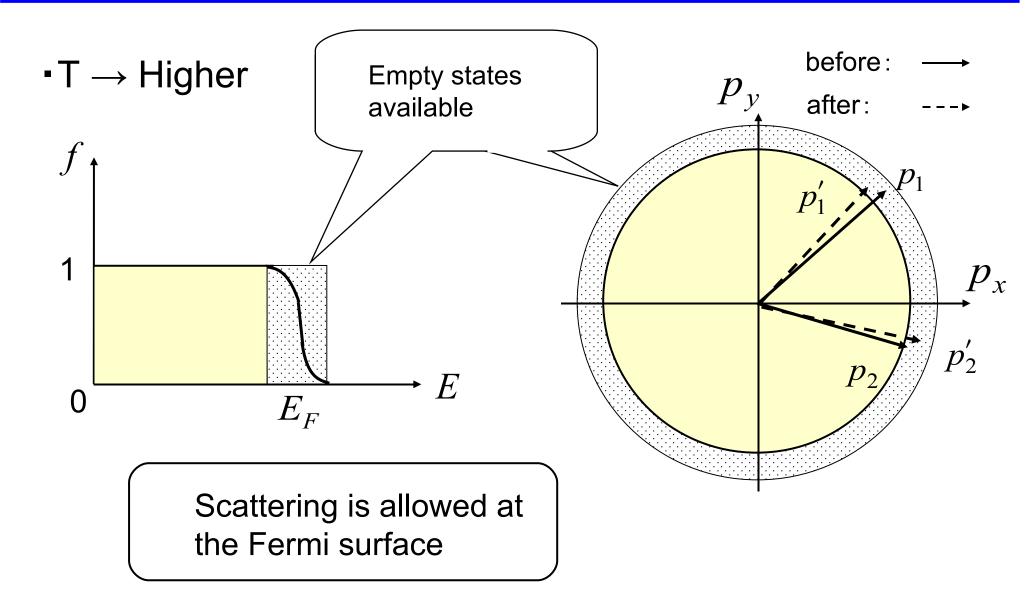


Spin Drag \Rightarrow strong temperature dependence

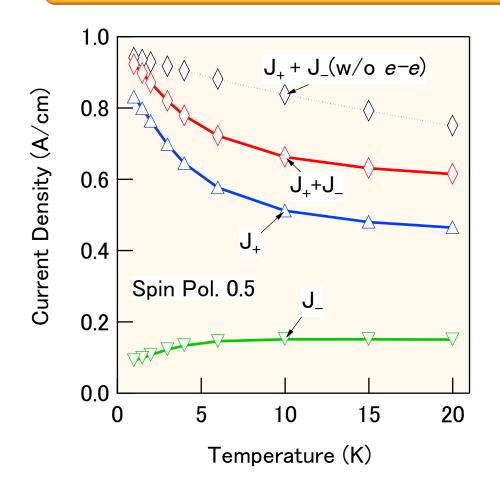
Electron-Electron scattering



Electron-Electron scattering



Current densities : J_+ , J_- and $J_+ + J_-$ for E = 10 V/cm at $n_+ + n_- = 2 \times 10^{11}$ cm⁻²

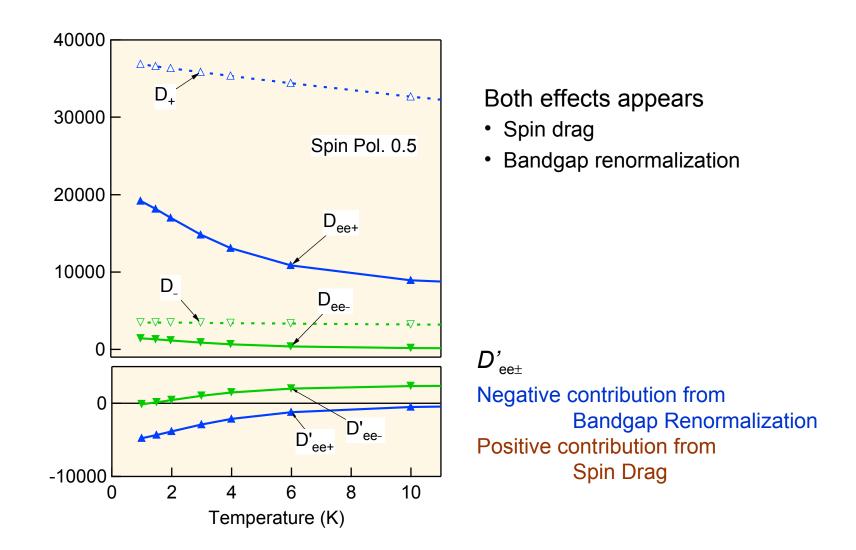


Spin drag effect appears (Bandgap renormalization is absent because of uniform distribution)

 J_{+} and J_{-} show characteristic temperature dependence

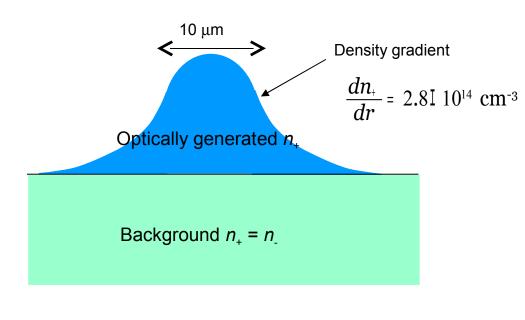
Total current $J_{+} + J_{-}$ also shows sublinear temperature dependence.

Diffusion coefficients $D_{ee\pm}$ vs. D_{\pm} at



Density gradient by optical excitations

Spin-up electrons are optically generated by a Gaussian-profile beam with circular polarization in a n-doped GaAs heterostructure.



No e-e interaction

 J_{+} flows outward $J_{-} = 0$

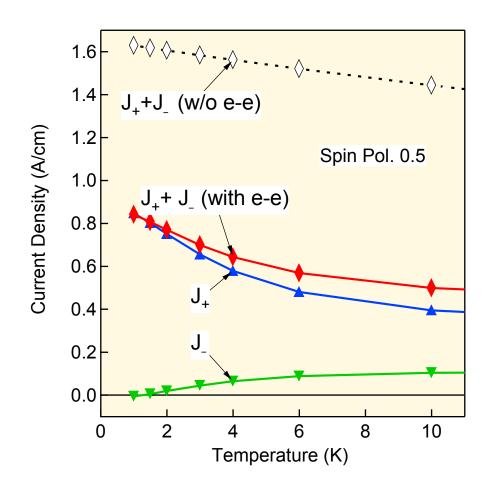
With e-e interaction

 J_{+} flows outward

flows outward by Spin Drag

flows inward by Energy renormalization

Diffusion current densities : J_{\pm} and $J_{ee\pm}$ at $n_{\pm} + n_{\pm} = 2 \times 10^{11} \text{ cm}^{-2}$



w/o e-e interaction J_+ only ($J_- = 0$)

with e-e interaction Finite J_{-}

J- is negative at the lowest temp. (inward flow)

$$\mathbf{J}_{+} = -qD_{ee+} \frac{\hbar n_{+}}{\hbar \mathbf{r}}$$
$$\mathbf{J}_{-} = -qD'_{ee+} \frac{\hbar n_{+}}{\hbar \mathbf{r}}$$

Conclusions

